

**Notic of Referenc s Cited**Application/Control No.  
10/066,627Applicant(s)/Patent Under  
Reexamination  
KATO ET AL.Examiner  
Maria GuerreroArt Unit  
2822

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**NON-PATENT DOCUMENTS**

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	U	R.C. Taylor et al. "LPCVD of Silicon Nitride Films From Hexachlorodisilane and Ammonia", 1988, Materials Research Society, Vol. 105, pages 319-324.
	V	Tanaka et al. "Film Properties of Low-k Silicon Nitride Films Formed by Hexachlorodisilane and Ammonia", 2000, Journal of The Electrochemical Society, pages 2284-2289.
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\*A copy of this reference is not being furnished with this Office action. (See MPEP § 707.05(a).)  
Dates in MM-YYYY format are publication dates. Classifications may be US or foreign.